

Data sheet acquired from Harris Semiconductor

CMOS Presettable Up/Down Counter

Binary or BCD-Decade High-Voltage Types (20-Volt Rating)

■ CD4029B consists of a four-stage binary or BCD-decade up/down counter with provisions for look-ahead carry in both counting modes. The inputs consist of a single CLOCK, CARRY-IN (CLOCK ENABLE), BINARY/DECADE, UP/DOWN, PRESET ENABLE, and four individual JAM signals. Q1, Q2, Q3, Q4 and a CARRY OUT signal are provided as outputs.

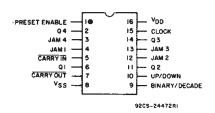
A high PRESET ENABLE signal allows information on the JAM INPUTS to preset the counter to any state asynchronously with the clock. A low on each JAM line, when the PRESET-ENABLE signal is high, resets the counter to its zero count. The counter is advanced one count at the positive transition of the clock when the CARRY-IN and PRE-SET ENABLE signals are low. Advancement is inhibited when the CARRY-IN or PRESET ENABLE signals are high. The CARRY-OUT signal is normally high and goes low when the counter reaches its maximum count in the UP mode or the minimum count in the DOWN mode provided the CARRY-IN signal is low. The CARRY-IN signal in the low state can thus be considered a CLOCK ENABLE. The CARRY-IN terminal must be connected to VSS when not in use.

Binary counting is accomplished when the BINARY/DECADE input is high; the counter counts in the decade mode when the BINARY/DECADE input is low. The counter counts up when the UP/DOWN input is high, and down when the UP/DOWN input is low. Multiple packages can be connected in either a parallel-clocking or a ripple-clocking arrangement as shown in Fig. 17.

Parallel clocking provides synchronous control and hence faster response from all counting outputs. Ripple-clocking allows for longer clock input rise and fall times.

The CD4029B-series types are supplied in 16-lead ceramic dual-in-line plastic packages (Esuffix), and in chip form (H suffix).

CD4029B Terminal Diagram



CD4029B Types

Features:

- Medium-speed operation . . . 8 MHz (typ.)
 - @ C_L = 50 pF and V_{DD}-V_{SS} = 10 V
- Multi-package parallel clocking for synchronous high speed output response or ripple clocking for slow clock input rise and fall times
- "Preset Enable" and individual "Jam" inputs provided
- Binary or decade up/down counting
- BCD outputs in decade mode
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range)

1 V at V_{DD} = 5 V

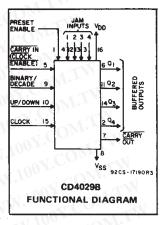
2 V at V_{DD} = 10 V

2.5 V at V_{DD} = 15 V

 Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Programmable binary and decade counting/frequency synthesizers-BCD output
- Analog to digital and digital to analog conversion
- Up/Down binary counting
- Magnitude and sign generation
- Up/Down decade counting
- Difference counting



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RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}$ C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V _{DD}	LIMITS		UNITS	
	(V)	Min.	Max.	Tag	
Supply-Voltage Range (For T _A = Full Package- Temperature Range)		3	18	V.100	
Setup Time t _{SU} : Càrry-In	5 10 15	200 70 60	<u> </u>	MAY TO	
U/D or B/D	5 10 15	340 140 100	-	ns	
Clock Pulse Width, tw	5 10 15	180 90 60	- - -		
Preset Enable Pulse Width, t _W	5 10 15	130 70 50	- - -		
Clock Input Frequency, f _{CL}	5 10 15	- - -	2 4 5.5	MHz	
Clock Rise and Fall Time, t _r CL, t _f CL	5 10 15	- - -	15	μς	

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MAXIMUM RATINGS, Absolute-Maximum Values:	
DC SUPPLY-VOLTAGE RANGE, (VDD)	
Voltages referenced to VSS Terminal)	0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	0.5V to V _{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -55°C to +100°C	500mW
For T _A = +100°C to +125°C	Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE	(All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (TA)	55°C to +125°C
STORAGE TEMPERATURE RANGE (Tstg)	65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ inch $(1.59 \pm 0.79$ mm) from c	ase for 10s max +265°C

	-		-		
SIA	1116	ELECT	RILAL	LHAHA	CTERISTICS

CHARAC- TERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							1 - Z C
	V _O (V)	VIN (V)	V _{DD}	_55	-40	+85	+125	Min.	+25 Typ.	Max.	s
	SIN.	0,5	5	5	5	150	150	_	0.04	5	(A)
Quiescent Device	_	0,10	10	10	10	≪ 300	300	WY	0.04	10	μА
Current,	-7//	0,15	15	20	20	600	600	=01	0.04	20	
IDD Max.	1/1	0,20	20	100	100	3000	3000	47	0.08	100	
0	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	097	mA
Output Low (Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-0	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	7-	
	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	1.10	
Output High (Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	- -≾±1\	
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	7-	
IOH Min.	13.5	0,15	15	-4.2	-4	-2.8	- 2.4	-3.4	-6.8	M.	
Output Voltage:	_	0,5	5	0.05			_	0	0.05	1.)\(\(\)	
Low-Level,	-	0,10	10	0.05			_	0	0.05		
VOL Max.	-	0,15	15	0.05			1/-	0	0.05	v	
Output	_	0,5	5	4.95			4.95	5	σ <u>e</u> V	11	
Voltage: High-Level,	_	0,10	10	9.95			9.95	10	-	W	
VOH Min.	_	0,15	15	14.95				14.95	15	7/	
Input Low Voltage V _{IL} Max.	0.5,4.5	-	5	1.5			(A)	_	1.5		
	1,9	-	10	3 N.CO				- m	N -	3	
	1.5,13.5		15	1 CC			77.	_	4	V	
Input High	0.5,4.5	_	5	3.5			3.5	_	_		
Voltage,	1,9	_	10	7			7	-	_		
V _{IH} Min.	1.5,13.5	_	15	11			11	-			
Input Current I _{IN} Max.	_	0,18	18	±0.1 ±0.1 ±1 ±1			_	±10 ⁻⁵	±0.1	μΑ	

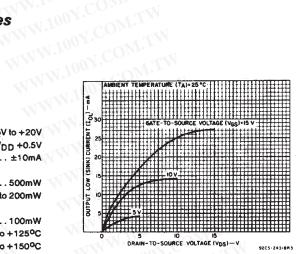


Fig. 1 - Typical output low (sink) current characteristics.

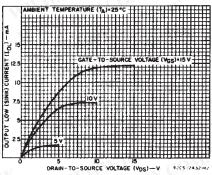


Fig. 2 - Minimum output low (sink) current characteristics.

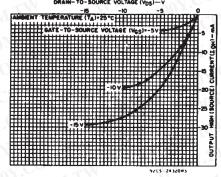
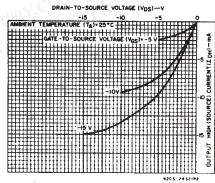


Fig. 3 - Typical output high (source) current characteristics.



Minimum output high (source) current characteristics.

CD4029B Types

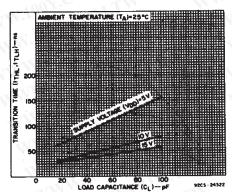


Fig. 5 — Typical transition time as a function of load capacitance.

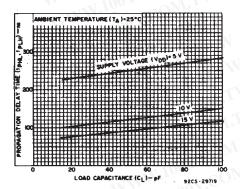


Fig. 6 — Typical propagation delay times as a function of load capacitance (Q output).

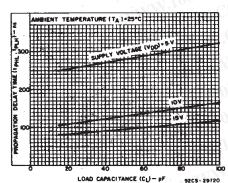


Fig. 7 – Typical propagation delay time as a function of load capacitance (carry output).

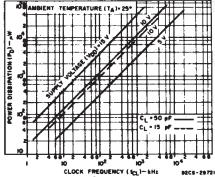
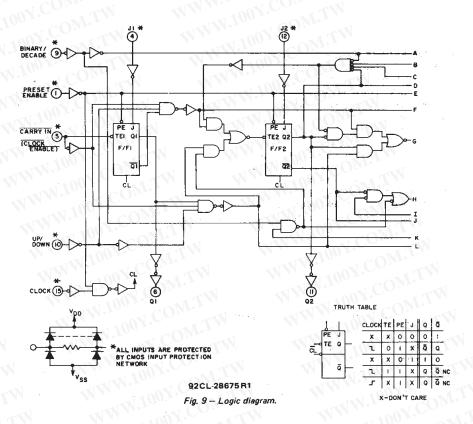


Fig. 8 – Typical power dissipation as a function of frequency.



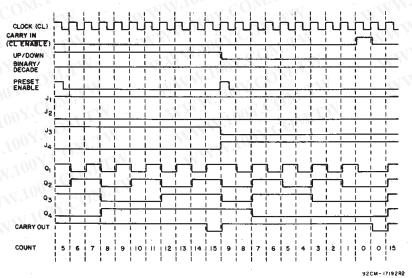


Fig. 10 - Timing diagram-binary mode.

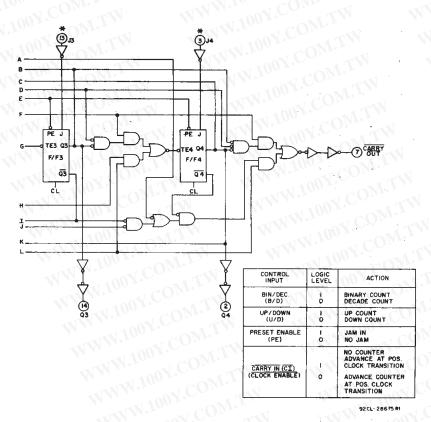


Fig. 9 - Logic diagram (cont'd).

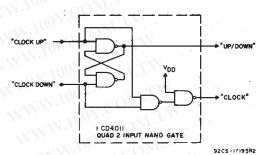


Fig. 11 — Conversion of clock up, clock down input signals to clock and up/down input signals.

The CD4029B CLOCK and UP/DOWN inputs are used directly in most applications. In applications where CLOCK UP and CLOCK DOWN inputs are provided, conversion to the CD4029B CLOCK and UP/DOWN inputs can easily be realized by use of the circuit in Fig. 11.

CD4029B changes count on positive transitions of CLOCK UP or CLOCK DOWN inputs. For the gate configuration shown below, when counting up the CLOCK DOWN input must be maintained high and conversely when counting down the CLOCK UP input must be maintained high.

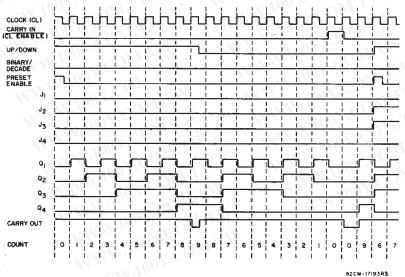


Fig. 12 - Timing diagram-decade mode

CD4029B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 k Ω

CHARACTERISTIC	TEST CO	TEST CONDITIONS		LIMITS		
W. T. COM.	WW	V _{DD} (V)	Min.	Тур.	Max.	UNIT
Clocked Operation	-3131	M.r.	J C	D IA =		N
Propagation Delay Time: tpHL, tpLH		5	-	250	500	
Q Output	W	10	1.Y	120	240	W
2017)		15	_	90	180	- 1
Carry Output	V	5	U(1,2)	280	560	IM
	}	10		130	260	- 1
		15	100	95	190	
TINN NOW TO COMME	!	5	-	100	200	ns
Transition Time: t _{THL} , t _{TLH}		10	1.50	50	100	N^{\cdot}
Q Outputs, Carry Output	N	15	-4	40	80	
			417	00		DM_{I}
Minimum Clock Pulse Width, tw	W.	5		90	180	- 1
Minimum Clock Pulse Width, tw	-31	10 15	44/	45 30	90 60	Ob
W. 1. 100 X	\mathcal{I}_{M}	15	_	30	90	
		5	1/1	-	15	CO
Clock Rise & Fall Time, t _r CL, t _f CL**		10	= 10	x : .)	15	μs
MAN. TOT CO.	W	15	12		15	1.0
Minimum Setup Times	M.r.	5	-0	170	340	-7 (
Minimum Setup Times, ts	WT 1	10	47	70	140	ns
B/D or U/D	\mathcal{O}_{MT}	15	50	50	100	
Maximum Clock Input Frequency, fCL	Time	5	2	4	11	MHz
	OM	10	4	8	W-2	
100	OM	15	5.5	111	121	
Input Capacitance, CIN	Any Input	7.1	_	5	7.5	ρF
Preset Enable	CON			W	di J	- 4
- 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	-100}	EST.		225	444	Q(-T)
Propagation Delay Time: tpHL, tpLH	17.0	5	-	235	470	
Q Outputs	~<1 CQ	15		100 80	200 160	
	001.			-00	100	
	-04.C	5	(- I	320	640	MAA
Carry Output	100 .	10	_	145	290	
	. MOY.	15	-	105	210	ns
	1.700	5		65	130	
Minimum Preset Enable Pulse Width, tw	1007	10	$J_{\overline{A}A}$	35	70	
-133	11.70	15		25	50	
Minimum Preset Enable Removal	100	5	(X_{i})	100	200	-
T:	111.	10	_ _ ()	55	110	
rime, trem*	- IN 19	15	N/= -	40	80	
Carry Input		10 X . C	110	LA		
Propagation Delay Time: tpHL, tpLH	M W.	5	_	170	340	
Carry Output	T XX	10	(A)	70	140	ns
,	WWW	15.		50	100	1
Min. HOLD Time	1	5	<u>~()</u>	25	50	ns
H*** Carry In	M M	10		15	30	ĺ
T	- 111	15	7 ES	12	25	
	AN A	- 100		100		ns
Min Set-Up Time	4 X T Y	5	-70		200	on I
s*** Carry In	77	10	77-	35	70	
	- 14	15	=7	30	60	- ▼

^{*} From Up/Down, Binary/Decode, Carry In, or Preset Enable Control Inputs to Clock Edge.

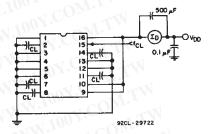


Fig. 13 - Power dissipation test circuit.

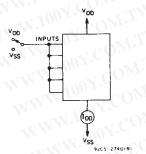


Fig. 14 - Quiescent-device current test circuit.

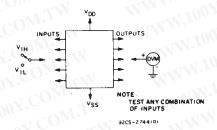


Fig. 15 - Input voltage test circuit.

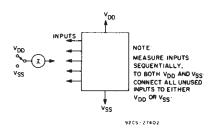
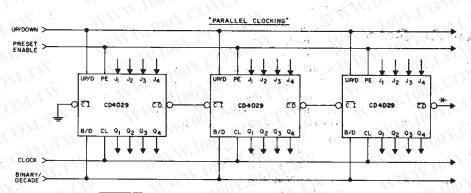


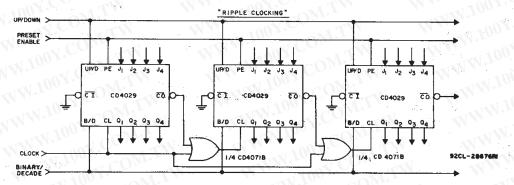
Fig. 16 - Input current test circuit.

^{**} If more than one unit is cascaded in the parallel clocked application, t_rCL should be made less than or equal to the sum of the fixed propagation delay at 15 pF and the transition time of the carry output driving stage for the estimated capacitive load. This measurement was made with a decoupling capacitor {>1 µF} between V_{DD} and V_{SS}.

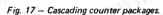
***From Carry In to Clock Edge

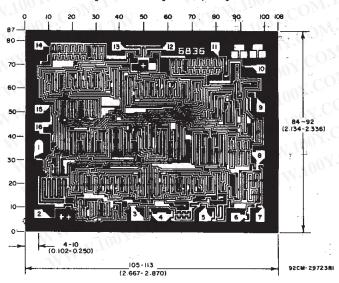


CARRY OUT lines at the 2nd, 3rd, etc., stages may have a negative-going glitch pulse resulting from differential delays of different CD4029B IC's. These negative-going glitches do not affect proper CD4029B operation. However, if the CARRY OUT signals are used to trigger other edge-sensitive logic devices, such as FF's or counters, the CARRY OUT signals should be gated with the clock signal using a 2-input OR gate such as CD4071B.



Ripple Clocking Mode: The Up/Down control can be changed at any count. The only restriction on changing the Up/Down control is that the clock input to the first counting stage must be high. For cascading counters operating in a fixed up-count or down-count mode, the OR gates are not required between stages, and $\overline{\text{CO}}$ is connected directly to the CL input of the next stage with $\overline{\text{CI}}$ grounded.





Chip dimensions and pad layout for CD4029B

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3}) inch).

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